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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M0
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	HDMI-CEC, I ² C, IrDA, LINbus, SPI, UART/USART
Peripherals	DMA, I ² S, POR, PWM, WDT
Number of I/O	27
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 13x12b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	32-UFQFN Exposed Pad
Supplier Device Package	32-UFQFPN (5x5)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f051k8u7

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

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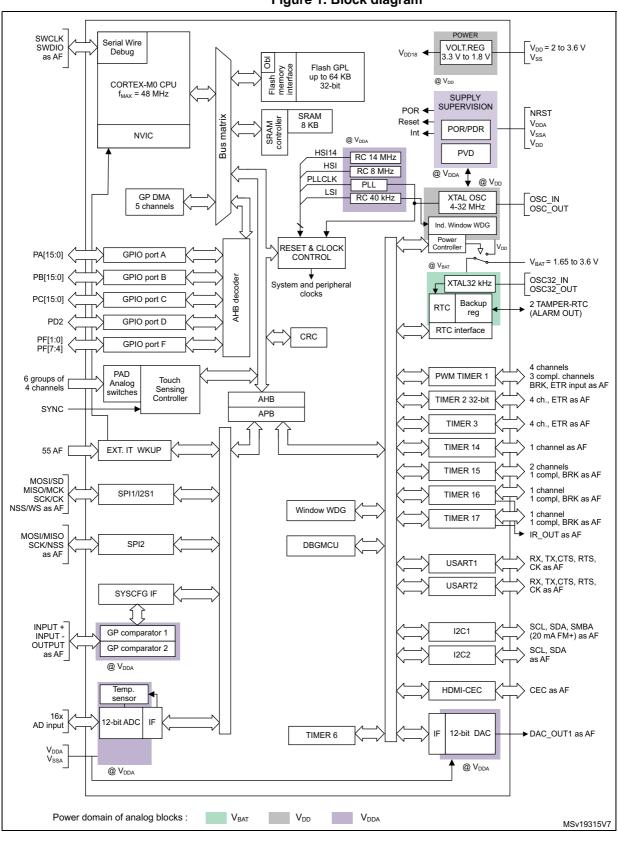


Figure 1. Block diagram



3 Functional overview

Figure 1 shows the general block diagram of the STM32F051xx devices.

3.1 ARM[®]-Cortex[®]-M0 core

The ARM[®] Cortex[®]-M0 is a generation of ARM 32-bit RISC processors for embedded systems. It has been developed to provide a low-cost platform that meets the needs of MCU implementation, with a reduced pin count and low-power consumption, while delivering outstanding computational performance and an advanced system response to interrupts.

The ARM[®] Cortex[®]-M0 processors feature exceptional code-efficiency, delivering the high performance expected from an ARM core, with memory sizes usually associated with 8- and 16-bit devices.

The STM32F051xx devices embed ARM core and are compatible with all ARM tools and software.

3.2 Memories

The device has the following features:

- 8 Kbytes of embedded SRAM accessed (read/write) at CPU clock speed with 0 wait states and featuring embedded parity checking with exception generation for fail-critical applications.
- The non-volatile memory is divided into two arrays:
 - 16 to 64 Kbytes of embedded Flash memory for programs and data
 - Option bytes

The option bytes are used to write-protect the memory (with 4 KB granularity) and/or readout-protect the whole memory with the following options:

- Level 0: no readout protection
- Level 1: memory readout protection, the Flash memory cannot be read from or written to if either debug features are connected or boot in RAM is selected
- Level 2: chip readout protection, debug features (Cortex[®]-M0 serial wire) and boot in RAM selection disabled

3.3 Boot modes

At startup, the boot pin and boot selector option bit are used to select one of the three boot options:

- boot from User Flash memory
- boot from System Memory
- boot from embedded SRAM

The boot loader is located in System Memory. It is used to reprogram the Flash memory by using USART on pins PA14/PA15 or PA9/PA10.



In Standby mode, it is put in power down mode. In this mode, the regulator output is in high impedance and the kernel circuitry is powered down, inducing zero consumption (but the contents of the registers and SRAM are lost).

3.5.4 Low-power modes

The STM32F051xx microcontrollers support three low-power modes to achieve the best compromise between low power consumption, short startup time and available wakeup sources:

Sleep mode

In Sleep mode, only the CPU is stopped. All peripherals continue to operate and can wake up the CPU when an interrupt/event occurs.

Stop mode

Stop mode achieves very low power consumption while retaining the content of SRAM and registers. All clocks in the 1.8 V domain are stopped, the PLL, the HSI RC and the HSE crystal oscillators are disabled. The voltage regulator can also be put either in normal or in low power mode.

The device can be woken up from Stop mode by any of the EXTI lines. The EXTI line source can be one of the 16 external lines, the PVD output, RTC, I2C1, USART1,, COMPx or the CEC.

The CEC, USART1 and I2C1 peripherals can be configured to enable the HSI RC oscillator so as to get clock for processing incoming data. If this is used when the voltage regulator is put in low power mode, the regulator is first switched to normal mode before the clock is provided to the given peripheral.

• Standby mode

The Standby mode is used to achieve the lowest power consumption. The internal voltage regulator is switched off so that the entire 1.8 V domain is powered off. The PLL, the HSI RC and the HSE crystal oscillators are also switched off. After entering Standby mode, SRAM and register contents are lost except for registers in the RTC domain and Standby circuitry.

The device exits Standby mode when an external reset (NRST pin), an IWDG reset, a rising edge on the WKUP pins, or an RTC event occurs.

Note: The RTC, the IWDG, and the corresponding clock sources are not stopped by entering Stop or Standby mode.

3.6 Clocks and startup

System clock selection is performed on startup, however the internal RC 8 MHz oscillator is selected as default CPU clock on reset. An external 4-32 MHz clock can be selected, in which case it is monitored for failure. If failure is detected, the system automatically switches back to the internal RC oscillator. A software interrupt is generated if enabled. Similarly, full interrupt management of the PLL clock entry is available when necessary (for example on failure of an indirectly used external crystal, resonator or oscillator).

Several prescalers allow the application to configure the frequency of the AHB and the APB domains. The maximum frequency of the AHB and the APB domains is 48 MHz.



The I/O configuration can be locked if needed following a specific sequence in order to avoid spurious writing to the I/Os registers.

3.8 Direct memory access controller (DMA)

The 5-channel general-purpose DMAs manage memory-to-memory, peripheral-to-memory and memory-to-peripheral transfers.

The DMA supports circular buffer management, removing the need for user code intervention when the controller reaches the end of the buffer.

Each channel is connected to dedicated hardware DMA requests, with support for software trigger on each channel. Configuration is made by software and transfer sizes between source and destination are independent.

DMA can be used with the main peripherals: SPIx, I2Sx, I2Cx, USARTx, all TIMx timers (except TIM14), DAC and ADC.

3.9 Interrupts and events

3.9.1 Nested vectored interrupt controller (NVIC)

The STM32F0xx family embeds a nested vectored interrupt controller able to handle up to 32 maskable interrupt channels (not including the 16 interrupt lines of Cortex[®]-M0) and 4 priority levels.

- Closely coupled NVIC gives low latency interrupt processing
- Interrupt entry vector table address passed directly to the core
- Closely coupled NVIC core interface
- Allows early processing of interrupts
- Processing of late arriving higher priority interrupts
- Support for tail-chaining
- Processor state automatically saved
- Interrupt entry restored on interrupt exit with no instruction overhead

This hardware block provides flexible interrupt management features with minimal interrupt latency.

3.9.2 Extended interrupt/event controller (EXTI)

The extended interrupt/event controller consists of 24 edge detector lines used to generate interrupt/event requests and wake-up the system. Each line can be independently configured to select the trigger event (rising edge, falling edge, both) and can be masked independently. A pending register maintains the status of the interrupt requests. The EXTI can detect an external line with a pulse width shorter than the internal clock period. Up to 55 GPIOs can be connected to the 16 external interrupt lines.

3.10 Analog-to-digital converter (ADC)

The 12-bit analog-to-digital converter has up to 16 external and 3 internal (temperature



3.14.2 General-purpose timers (TIM2, 3, 14, 15, 16, 17)

There are six synchronizable general-purpose timers embedded in the STM32F051xx devices (see *Table 7* for differences). Each general-purpose timer can be used to generate PWM outputs, or as simple time base.

TIM2, TIM3

STM32F051xx devices feature two synchronizable 4-channel general-purpose timers. TIM2 is based on a 32-bit auto-reload up/downcounter and a 16-bit prescaler. TIM3 is based on a 16-bit auto-reload up/downcounter and a 16-bit prescaler. They feature 4 independent channels each for input capture/output compare, PWM or one-pulse mode output. This gives up to 12 input captures/output compares/PWMs on the largest packages.

The TIM2 and TIM3 general-purpose timers can work together or with the TIM1 advancedcontrol timer via the Timer Link feature for synchronization or event chaining.

TIM2 and TIM3 both have independent DMA request generation.

These timers are capable of handling quadrature (incremental) encoder signals and the digital outputs from 1 to 3 hall-effect sensors.

Their counters can be frozen in debug mode.

TIM14

This timer is based on a 16-bit auto-reload upcounter and a 16-bit prescaler.

TIM14 features one single channel for input capture/output compare, PWM or one-pulse mode output.

Its counter can be frozen in debug mode.

TIM15, TIM16 and TIM17

These timers are based on a 16-bit auto-reload upcounter and a 16-bit prescaler.

TIM15 has two independent channels, whereas TIM16 and TIM17 feature one single channel for input capture/output compare, PWM or one-pulse mode output.

The TIM15, TIM16 and TIM17 timers can work together, and TIM15 can also operate with TIM1 via the Timer Link feature for synchronization or event chaining.

TIM15 can be synchronized with TIM16 and TIM17.

TIM15, TIM16 and TIM17 have a complementary output with dead-time generation and independent DMA request generation.

Their counters can be frozen in debug mode.

3.14.3 Basic timer TIM6

This timer is mainly used for DAC trigger generation. It can also be used as a generic 16-bit time base.

3.14.4 Independent watchdog (IWDG)

The independent watchdog is based on an 8-bit prescaler and 12-bit downcounter with user-defined refresh window. It is clocked from an independent 40 kHz internal RC and as it operates independently from the main clock, it can operate in Stop and Standby modes. It



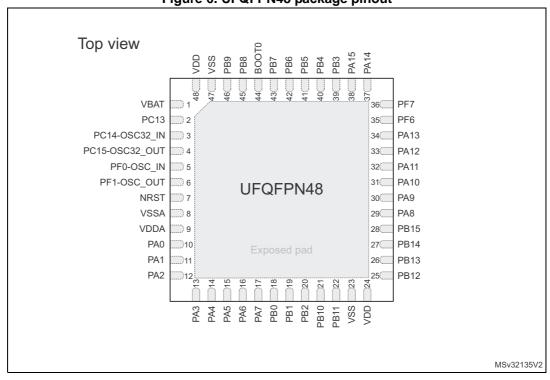
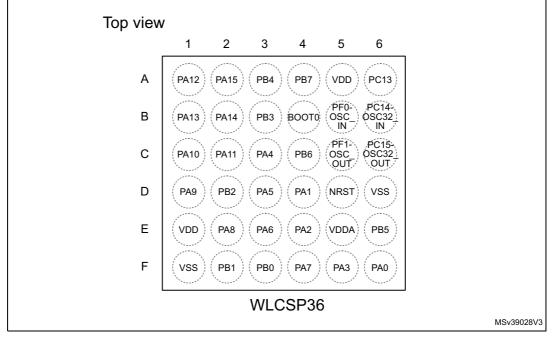


Figure 6. UFQFPN48 package pinout

Figure 7. WLCSP36 package pinout



1. The above figure shows the package in top view, changing from bottom view in the previous document versions.



	P	Pin nu	umbe	er						-	nctions
LQFP64	UFBGA64	LQFP48/UFQFPN48	WLCSP36	LQFP32	UFQFPN32	Pin name (function upon reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
33	H8	25	-	-	-	PB12	I/O	FT	(5)	SPI2_NSS, TIM1_BKIN, TSC_G6_IO2, EVENTOUT	-
34	G8	26	-	-	-	PB13	I/O	FT	(5)	SPI2_SCK, TIM1_CH1N, TSC_G6_IO3	-
35	F8	27	-	-	-	PB14	I/O	FT	(5)	SPI2_MISO, TIM1_CH2N, TIM15_CH1, TSC_G6_IO4	-
36	F7	28	-	-	-	PB15	I/O	FT	(5)	SPI2_MOSI, TIM1_CH3N, TIM15_CH1N, TIM15_CH2	RTC_REFIN
37	F6	-	-	-	-	PC6	I/O	FT	-	TIM3_CH1	-
38	E7	-	-	-	-	PC7	I/O	FT	-	TIM3_CH2	-
39	E8	-	-	-	-	PC8	I/O	FT	-	TIM3_CH3	-
40	D8	-	-	-	-	PC9	I/O	FT	-	TIM3_CH4	-
41	D7	29	E2	18	18	PA8	I/O	FT	-	USART1_CK, TIM1_CH1, EVENTOUT, MCO	-
42	C7	30	D1	19	19	PA9	I/O	FT	-	USART1_TX, TIM1_CH2, TIM15_BKIN, TSC_G4_IO1	-
43	C6	31	C1	20	20	PA10	I/O	FT	-	USART1_RX, TIM1_CH3, TIM17_BKIN, TSC_G4_IO2	-
44	C8	32	C2	21	21	PA11	I/O	FT	-	USART1_CTS, TIM1_CH4, COMP1_OUT, TSC_G4_IO3, EVENTOUT	-

Table 13. Pin definitions (continued)



				AI	periph	erals en	abled	All peripherals disabled				
Symbol	Parameter	Conditions	f _{HCLK}	Tun	Μ	lax @ T,	A ⁽¹⁾	Tun	Max @ T _A ⁽¹⁾			Unit
				Тур	25 °C	85 °C	105 °C	Тур	25 °C	85 °C	105 °C	
	HSE	48 MHz	14.0	15.3 ⁽²⁾	15.3	16.0 ⁽²⁾	2.8	3.0 ⁽²⁾	3.0	3.2 ⁽²⁾		
		bypass, PLL on	32 MHz	9.5	10.2	10.2	10.7	2.0	2.1	2.1	2.3	
	Supply		24 MHz	7.3	7.8	7.8	8.3	1.5	1.7	1.7	1.9	
		HSE bypass, PLL off	8 MHz	2.6	2.9	2.9	3.0	0.6	0.8	0.8	0.8	
I _{DD}	current in Sleep		1 MHz	0.4	0.6	0.6	0.6	0.2	0.4	0.4	0.4	mA
	mode		48 MHz	14.0	15.3	15.3	16.0	3.8	4.0	4.1	4.2	
		HSI clock, PLL on	32 MHz	9.5	10.2	10.2	10.7	2.6	2.7	2.8	2.8	
			24 MHz	7.3	7.8	7.8	8.3	2.0	2.1	2.1	2.1	
		HSI clock, PLL off	8 MHz	2.6	2.9	2.9	3.0	0.6	0.8	0.8	0.8	

Table 25. Typical and maximum current consumption from V_{DD} at 3.6 V (continued)

1. Data based on characterization results, not tested in production unless otherwise specified.

2. Data based on characterization results and tested in production (using one common test limit for sum of I_{DD} and I_{DDA}).

					V _{DDA}	= 2.4 V		V _{DDA} = 3.6 V				
Symbol	Parameter	Conditions (1)	f _{HCLK}	Turn	М	Max @ T _A ⁽²⁾			Max @ T _A ⁽²⁾			Unit
				Тур	25 °C	85 °C	105 °C	Тур	25 °C	85 °C	105 °C	
		HSE	48 MHz	150	170 ⁽³⁾	178	182 ⁽³⁾	164	183 ⁽³⁾	195	198 ⁽³⁾	
Supply current in	bypass,	32 MHz	104	121	126	128	113	129	135	138		
		PLL on	24 MHz	82	96	100	103	88	102	106	108	
	Run or Sleep	eep bypass, ode, PLL off	8 MHz	2.0	2.7	3.1	3.3	3.5	3.8	4.1	4.4	
I _{DDA}	mode, code		1 MHz	2.0	2.7	3.1	3.3	3.5	3.8	4.1	4.4	μA
	executing		48 MHz	220	240	248	252	244	263	275	278	
	from Flash memory or	HSI clock, PLL on	32 MHz	174	191	196	198	193	209	215	218	
	RAM		24 MHz	152	167	173	174	168	183	190	192	
		HSI clock, PLL off	8 MHz	72	79	82	83	83.5	91	94	95	

Table 26. Typical and maximum current consumption from the $\rm V_{DDA}$ supply

 Current consumption from the V_{DDA} supply is independent of whether the digital peripherals are enabled or disabled, being in Run or Sleep mode or executing from Flash memory or RAM. Furthermore, when the PLL is off, I_{DDA} is independent of clock frequencies.

2. Data based on characterization results, not tested in production unless otherwise specified.

3. Data based on characterization results and tested in production (using one common test limit for sum of I_{DD} and I_{DDA}).



	Parameter		Typ @ V _{BAT}									
Symbol		Conditions	1.65 V	1.8 V	2.4 V	2.7 V	3.3 V	3.6 V	T _A = 25 ℃	T _A = 85 ℃	T _A = 105 °C	Unit
I _{DD_VBAT}	RTC domain supply current	LSE & RTC ON; "Xtal mode": lower driving capability; LSEDRV[1:0] = '00'	0.5	0.5	0.6	0.7	0.8	0.9	1.0	1.3	1.7	
		LSE & RTC ON; "Xtal t mode" higher driving		1.6	2.1	μA						

Table 28. Typical and maximum current consumption from the $\rm V_{BAT}$ supply

1. Data based on characterization results, not tested in production.

Typical current consumption

The MCU is placed under the following conditions:

- V_{DD} = V_{DDA} = 3.3 V
- All I/O pins are in analog input configuration
- The Flash memory access time is adjusted to f_{HCLK} frequency:
 - 0 wait state and Prefetch OFF from 0 to 24 MHz
 - 1 wait state and Prefetch ON above 24 MHz
- When the peripherals are enabled, f_{PCLK} = f_{HCLK}
- PLL is used for frequencies greater than 8 MHz
- AHB prescaler of 2, 4, 8 and 16 is used for the frequencies 4 MHz, 2 MHz, 1 MHz and 500 kHz respectively



1. Guaranteed by design, not tested in production.

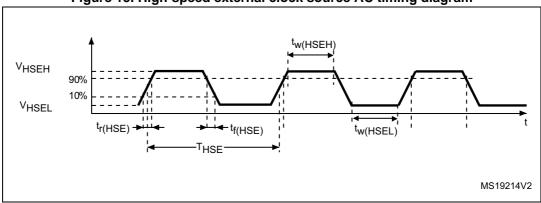


Figure 15. High-speed external clock source AC timing diagram

Low-speed external user clock generated from an external source

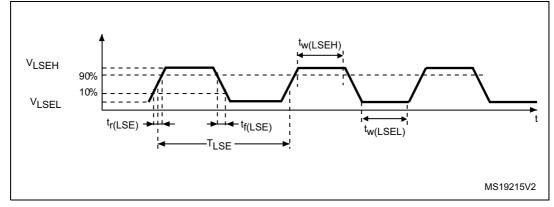
In bypass mode the LSE oscillator is switched off and the input pin is a standard GPIO.

The external clock signal has to respect the I/O characteristics in *Section 6.3.14*. However, the recommended clock input waveform is shown in *Figure 16*.

Symbol	Parameter ⁽¹⁾	Min	Тур	Max	Unit
f _{LSE_ext}	User external clock source frequency	-	32.768	1000	kHz
V _{LSEH}	OSC32_IN input pin high level voltage	0.7 V _{DDIOx}	-	V _{DDIOx}	V
V_{LSEL}	OSC32_IN input pin low level voltage	V _{SS}	-	0.3 V _{DDIOx}	v
t _{w(LSEH)} t _{w(LSEL)}	OSC32_IN high or low time	450	-	-	ns
t _{r(LSE)} t _{f(LSE)}	OSC32_IN rise or fall time	-	-	50	115

Table 34. Low-speed external user clock characteristics

1. Guaranteed by design, not tested in production.







High-speed external clock generated from a crystal/ceramic resonator

The high-speed external (HSE) clock can be supplied with a 4 to 32 MHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on design simulation results obtained with typical external components specified in *Table 35*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Symbol	Parameter	Conditions ⁽¹⁾	Min ⁽²⁾	Тур	Max ⁽²⁾	Unit
f _{OSC_IN}	Oscillator frequency	-	4	8	32	MHz
R _F	Feedback resistor	-	-	200	-	kΩ
		During startup ⁽³⁾ - - 8.5 $V_{DD} = 3.3 \text{ V},$ - 0.4 - CL = 10 pF@8 MHz - 0.4 - $V_{DD} = 3.3 \text{ V},$ - 0.5 - CL = 10 pF@8 MHz - 0.5 - CL = 10 pF@8 MHz - 0.5 -				
		Rm = 30 Ω,	-	0.4	-	
		Rm = 45 Ω,	-	0.5	-	
I _{DD}	HSE current consumption	V _{DD} = 3.3 V, Rm = 30 Ω, CL = 5 pF@32 MHz	-	0.8	-	mA
		V _{DD} = 3.3 V, Rm = 30 Ω, CL = 10 pF@32 MHz	-	1	-	
		V _{DD} = 3.3 V, Rm = 30 Ω, CL = 20 pF@32 MHz	-	1.5	-	
9 _m	Oscillator transconductance	Startup	10	-	-	mA/V
$t_{\rm SU(HSE)}^{(4)}$	Startup time	V _{DD} is stabilized	-	2	-	ms

1. Resonator characteristics given by the crystal/ceramic resonator manufacturer.

2. Guaranteed by design, not tested in production.

3. This consumption level occurs during the first 2/3 of the $t_{SU(\text{HSE})}$ startup time

 t_{SU(HSE)} is the startup time measured from the moment it is enabled (by software) to a stabilized 8 MHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer

For C_{L1} and C_{L2} , it is recommended to use high-quality external ceramic capacitors in the 5 pF to 20 pF range (Typ.), designed for high-frequency applications, and selected to match the requirements of the crystal or resonator (see *Figure 17*). C_{L1} and C_{L2} are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2} . PCB and MCU pin capacitance must be included (10 pF can be used as a rough estimate of the combined pin and board capacitance) when sizing C_{L1} and C_{L2} .

Note: For information on selecting the crystal, refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website www.st.com.



Software recommendations

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical Data corruption (for example control registers)

Prequalification trials

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the Oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

Electromagnetic Interference (EMI)

The electromagnetic field emitted by the device are monitored while a simple application is executed (toggling 2 LEDs through the I/O ports). This emission test is compliant with IEC 61967-2 standard which specifies the test board and the pin loading.

Symbol	Parameter	Conditions	Monitored	Max vs. [f _{HSE} /f _{HCLK}]	Unit
Cymbol	frequency ba		frequency band	8/48 MHz	onit
	Peak level	V_{DD} = 3.6 V, T_A = 25 °C, LQFP64 package compliant with IEC 61967-2	0.1 to 30 MHz	-3	
6			30 to 130 MHz	28	dBµV
S _{EMI}	reak level		130 MHz to 1 GHz	23	
			EMI Level	4	-

Table 44. EMI characteristics

6.3.12 Electrical sensitivity characteristics

Based on three different tests (ESD, LU) using specific measurement methods, the device is stressed in order to determine its performance in terms of electrical sensitivity.

Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts \times (n+1) supply pins). This test conforms to the JESD22-A114/C101 standard.



Symbol	Parameter	Conditio	ons	Min ⁽¹⁾	Тур	Max ⁽¹⁾	Unit
		No hysteresis (COMPxHYST[1:0]=00)	-	-	0	-	
		High speed mode	3		13		
		Low hysteresis (COMPxHYST[1:0]=01	All other power modes	5	8	10	mV
V _{hys}	Comparator hysteresis	Medium hysteresis (COMPxHYST[1:0]=10)	High speed mode	7		26	
			All other power modes	9	15	19	
		High bystorosis	High speed mode	18		49	
		High hysteresis (COMPxHYST[1:0]=11)	All other power modes	19	31	40	

Table 56. Comparator characteristics (continued)

1. Data based on characterization results, not tested in production.

2. For more details and conditions see Figure 28: Maximum V_{REFINT} scaler startup time from power down.

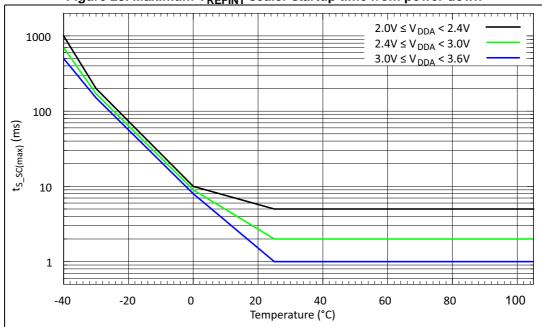


Figure 28. Maximum V_{REFINT} scaler startup time from power down



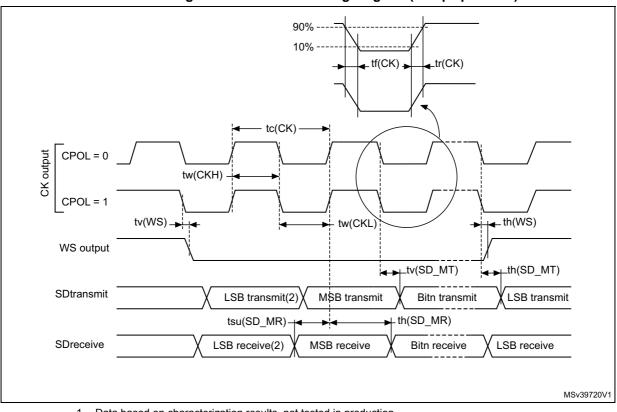


Figure 33. I²S master timing diagram (Philips protocol)

- 1. Data based on characterization results, not tested in production.
- 2. LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.



Device marking

The following figure gives an example of topside marking orientation versus ball A1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

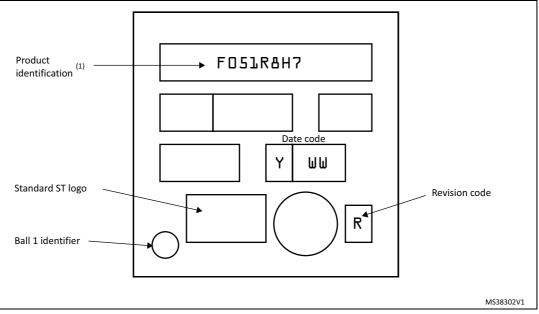


Figure 36. UFBGA64 package marking example

 Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.



Device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

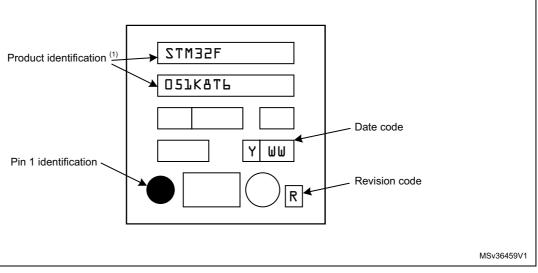


Figure 51. LQFP32 package marking example

 Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.

7.7 UFQFPN32 package information

UFQFPN32 is a 32-pin, 5x5 mm, 0.5 mm pitch ultra-thin fine-pitch quad flat package.



		millimeters			inches ⁽¹⁾	
Symbol	Min	Тур	Мах	Min	Тур	Мах
А	0.500	0.550	0.600	0.0197	0.0217	0.0236
A1	0.000	0.020	0.050	0.0000	0.0008	0.0020
A3	-	0.152	-	-	0.0060	-
b	0.180	0.230	0.280	0.0071	0.0091	0.0110
D	4.900	5.000	5.100	0.1929	0.1969	0.2008
D1	3.400	3.500	3.600	0.1339	0.1378	0.1417
D2	3.400	3.500	3.600	0.1339	0.1378	0.1417
E	4.900	5.000	5.100	0.1929	0.1969	0.2008
E1	3.400	3.500	3.600	0.1339	0.1378	0.1417
E2	3.400	3.500	3.600	0.1339	0.1378	0.1417
е	-	0.500	-	-	0.0197	-
L	0.300	0.400	0.500	0.0118	0.0157	0.0197
ddd	-	-	0.080	-	-	0.0031

Table 73. UFQFPN32 package mechanical data

1. Values in inches are converted from mm and rounded to 4 decimal digits.

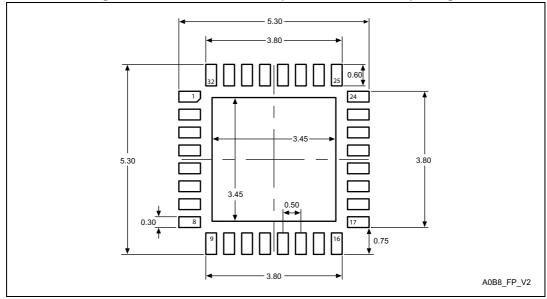


Figure 53. Recommended footprint for UFQFPN32 package

1. Dimensions are expressed in millimeters.





9 Revision history

Date	Revision	Changes
05-Apr-2012	1	Initial release
25-Apr-2012	2	Updated <i>Table: STM32F051xx family device features and peripheral counts</i> for SPI and I ² C in 32-pin package.
		Corrected Group 3 pin order in <i>Table: Capacitive sensing GPIOs available on STM32F051xx devices.</i>
		Updated the current consumption values in Section: Electrical characteristics.
		Updated Table: HSI14 oscillator characteristics
23-Jul-2012	3	Features reorganized and <i>Figure: Block diagram</i> structure changed.
		Added LQFP32 package.
		Updated Section: Cyclic redundancy check calculation unit (CRC).
		Modified the number of priority levels in Section: Nested vectored interrupt controller (NVIC).
		Added note 3. for PB2 and PB8, changed TIM2_CH_ETR into TIM2_CH1_ETR in <i>Table: Pin definitions</i> and <i>Table: Alternate functions selected through GPIOA_AFR registers for port A.</i> Added <i>Table: Alternate functions selected through GPIOB_AFR registers for port B.</i>
		Updated I _{VDD} , I _{VSS} , and I _{INJ(PIN)} in <i>Table: Current characteristics.</i>
		Updated ACC _{HSI} in <i>Table: HSI oscillator characteristics</i> and <i>Table: HSI14 oscillator characteristics</i> .
		Updated Table: I/O current injection susceptibility.
		Added BOOT0 input low and high level voltage in <i>Table: I/O</i> static characteristics.
		Modified number of pins in V _{OL} and V _{OH} description, and changed condition for V _{OLFM+} in <i>Table: Output voltage characteristics.</i>
		Changed V_{DD} to V_{DDA} in Figure: Typical connection diagram using the ADC.
		Updated Ts_temp in Table: TS characteristics.
		Updated Figure: I/O AC characteristics definition.

Table 76. Document revision history



Date	Revision	Changes
Date	Revision	
28-Aug-2015	5	 Updated the following: DAC and power management feature descriptions in <i>Features</i> Table 2: STM32F051xx family device features and peripheral count Section 3.5.1: Power supply schemes Figure 13: Power supply scheme Table 17: Voltage characteristics Table 20: General operating conditions: updated the footnote for V_{IN} parameter Table 28: Typical and maximum current consumption from the V_{BAT} supply Table 52: ADC characteristics Table 33: High-speed external user clock characteristics: replaced V_{DD} with V_{DDIOX} Table 34: Low-speed external user clock characteristics: replaced V_{DD} with V_{DDIOX} Table 37: HSI oscillator characteristics and Figure 19: HSI oscillator characteristics: changed the min value for ACC_{HSI14} Table 41: Flash memory characteristics: changed the values for t_{ME} and I_{DD} in write mode Table 43: EMS characteristics changed the value of V_{EFTB} Table 43: EMS characteristics changed the value of V_{EFTB} Figure 10: STM32F051x8 memory map Figure 21: TC and TTa I/O input characteristics Figure 22: Five volt tolerant (FT and FTf) I/O input characteristics Figure 23: I/O AC characteristics: changed the description and values for V_{SC}, V_{DDA} and V_{REFINT} parameters. Added Figure 28: Maximum V_{REFINT} parameters. Added Figure 28: Maximum V_{REFINT} parameters. Added Figure 28: Maximum V_{REFINT} parameters. Section 6.3:2: Communication interfaces: updated the min value for T_S-v_{bat} and the typical value for R parameters Section and features in the subsection I²C interface characteristics: Table 57: TS characteristics: updated the min value for Ts - temp Table 58: V_{BAT} monitoring characteristics: changed the min value for Ts-v_{bat} and the typical value for R parameters Section 6.3:2: Communication interfaces: updated the description and features in the subsection I²C interface cha

Table 76. Document revision history (continued)

